

ABSTRACT OF THE DISCLOSURE

In a semiconductor device in which the gate electrode of a MISFET formed on a semiconductor substrate is electrically connected to a well region under the channel of the MISFET, the MISFET is formed in an island-shaped element region formed on the semiconductor substrate, and electrical connection between the gate electrode of the MISFET and the well region in the semiconductor substrate is done on the side surface of the island-shaped element region.